

# High-fidelity Quantum Gates in Silicon Quantum Computing

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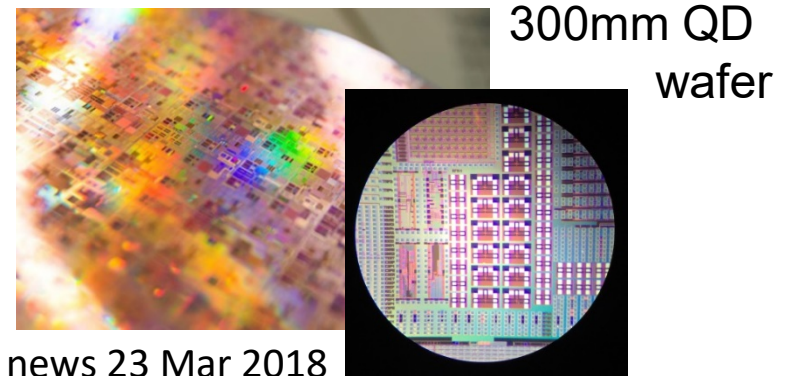
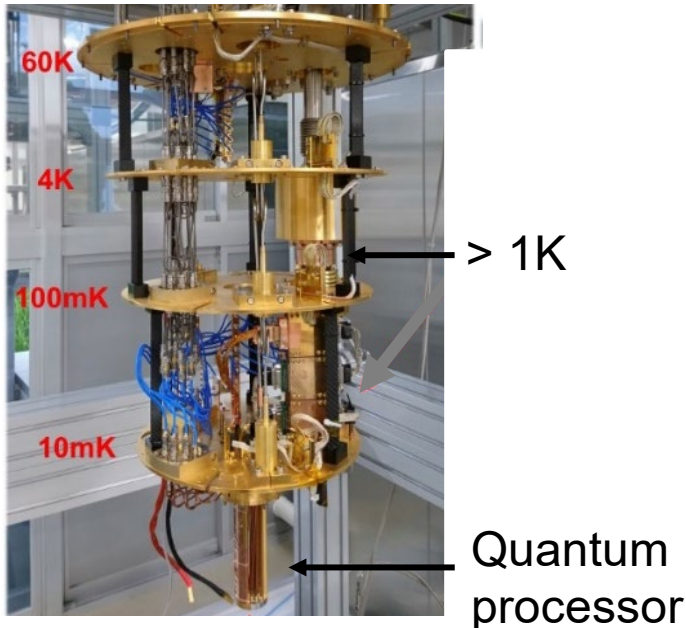
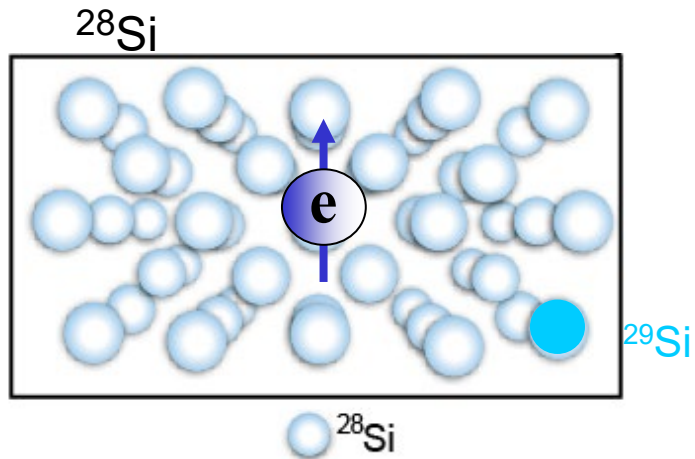
# Why Silicon?

No abundant nuclear spin ( $^{29}\text{Si}$ )  
4.7% in Nat. Si, < 0.1 % in  $^{28}\text{Si}$

→ Long coherence time  
> 10 msec

Compatibility of device fabrication with  
industrial technology

→  $10^9$  bits/cm<sup>2</sup> on a chip



High temperature operation at > 1K

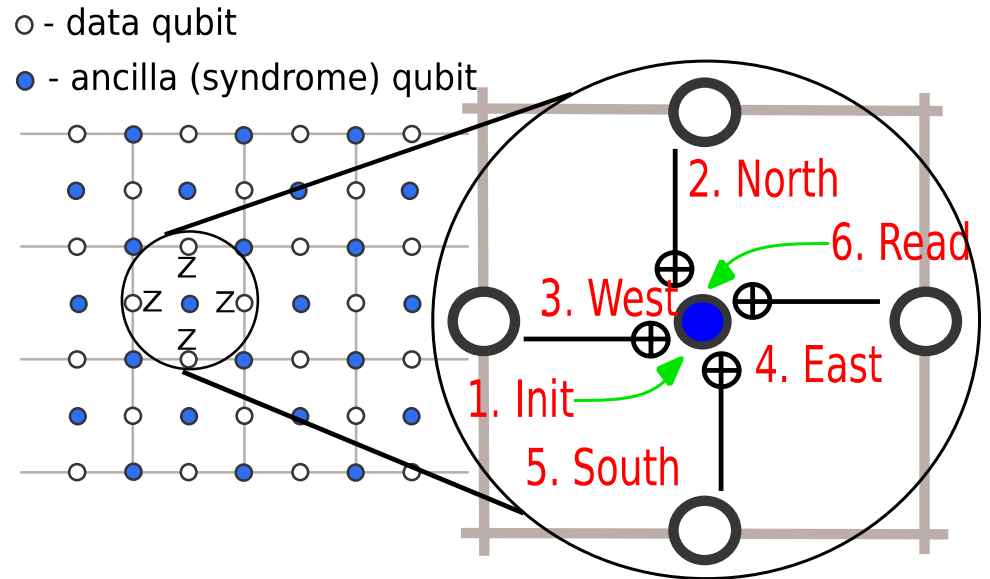
→ Cooling power at 1 K X100 larger than  
at < 0.1 K  
.... helpful for more qubits  
and cryo-electronics

# Fidelity Thresholds for Fault Tolerant QC

## Error correction thresholds

- Fidelity (1 qubit) > 99.9%
- Fidelity (2 qubit) > 99%
- Initialization F > 99%
- Readout F > 99%

## Error Correction in Surface Code



A. G. Fowler et al., Phys. Rev. A (2009)

# Fidelity of Single and Two-qubit Gates

| Materials             | Single qubit gate                          |                 | Two-qubit gate  |
|-----------------------|--|-----------------|---|
|                       | Spin-1/2                                   | Singlet-triplet | Spin-1/2  |
| Nat. Si/SiGe          | F = 99.6% [1]<br>Limited by magnetic noise | F = 99.6% [2]   | F = 98% [3], 75% [5]<br>(ST F $\approx$ SWAP F = 99.6% [2]<br>Limited by magnetic noise |
| <sup>28</sup> Si/SiGe | F = 99.93% [4]<br>Limited by charge noise  |                 |   |
| <sup>28</sup> SiMOS   | F = 99.96% [6]<br>Limited by charge noise  |                 | F <sub>Clifford</sub> = 95%, F <sub>CROT</sub> = 98% [7]                                |

[1] K. Takeda et al. Sci. Adv. 2016.

[2] K. Takeda et al. arXiv:1910.00771.

[3] X. Xue et al. PRX 2019.

[4] J. Yoneda et al. Nat. Nanotechnol. 2018.

[5] DM. Zajac et al. Science 2018.

[6] C. H. Yang et al., Nat. Electron. 2019.

[7] W. Huang et al. Nature 2019.

F > 99% on arXiv  
for two electron spins in  
<sup>28</sup>Si/SiGe from TuDelft  
and this work  
for two nuclear spins in <sup>28</sup>Si  
from UNSW

# Outline

## **High-fidelity single and two qubit gates**

- Single and two qubit gates with fast qubit gating and long dephasing time

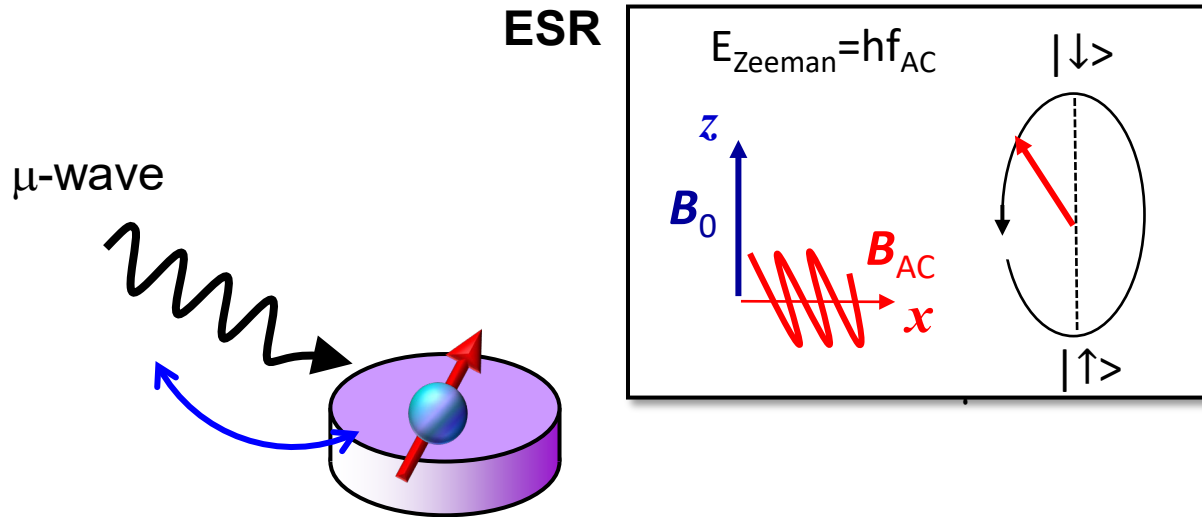
## **High-fidelity readout and initialization**

- Quantum non-demolition measurement

## **Three qubit entanglement**

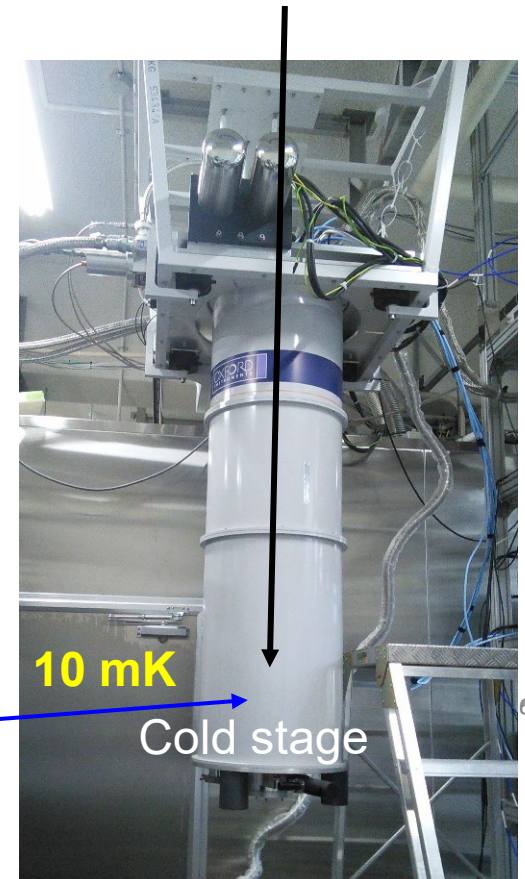
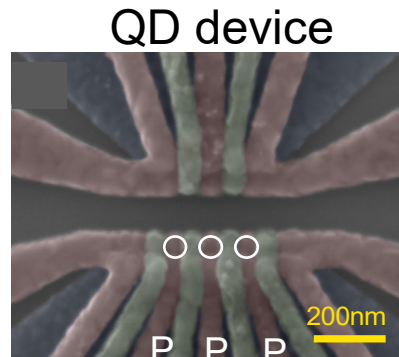
- Preparation of GHZ state

# Physical Implementation of Spin Qubits : Spin Resonance for Single Electrons in QD

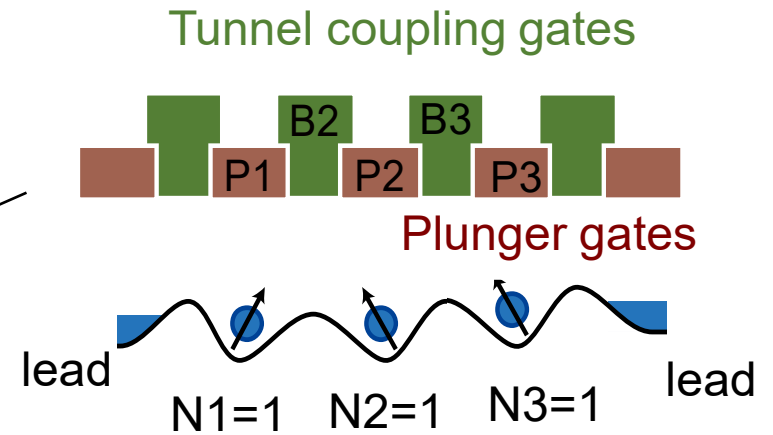
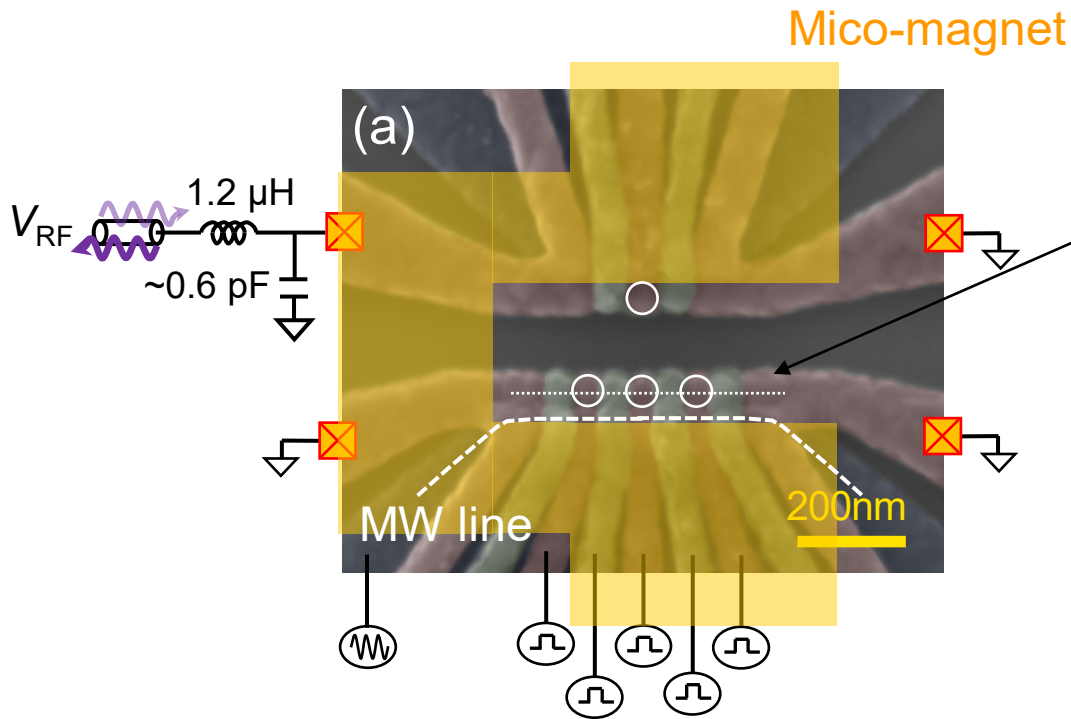


E to B conversion by spin-electric coupling  
( $\mu$ -magnet, spin-orbit, mini-coil,...)

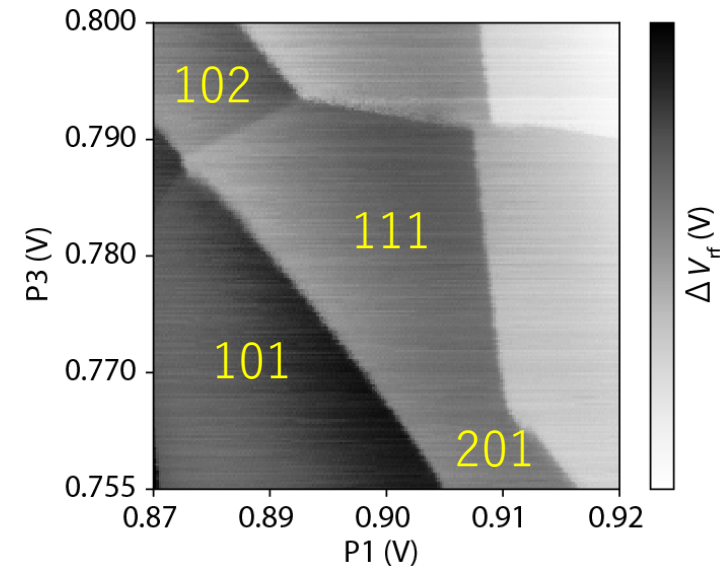
- Y. Tokura et al. PRL 2007
- MP Ladriere et al. Nat. Phys. 2010
- R. Brenner et al. PRL 2010
- K. Takeda et al. Sci. Adv. 2016
- J. Yoneda et al. Nat. Nano. 2018
- ....



# Three Qubit Device with Three QDs



Charge state diagram

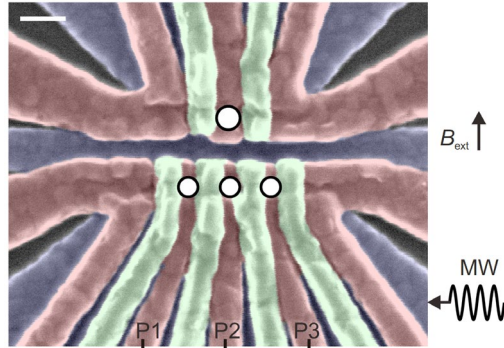


- Three QDs for making qubits and one QD for detecting electron occupations in each QD.
- Co micro-magnet on top

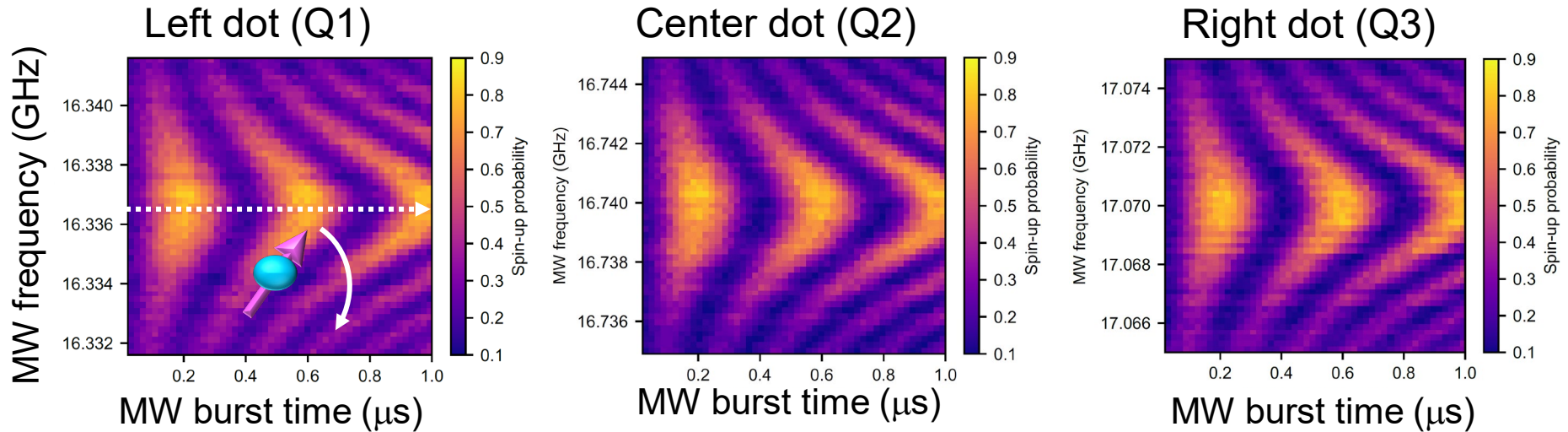


# Three Spin Qubits in Si Triple QD

Takeda et al. Nat. Nanotechnol. 2021



$^{28}\text{Si}/\text{SiGe}$  from G. Scappucci TuDelft.



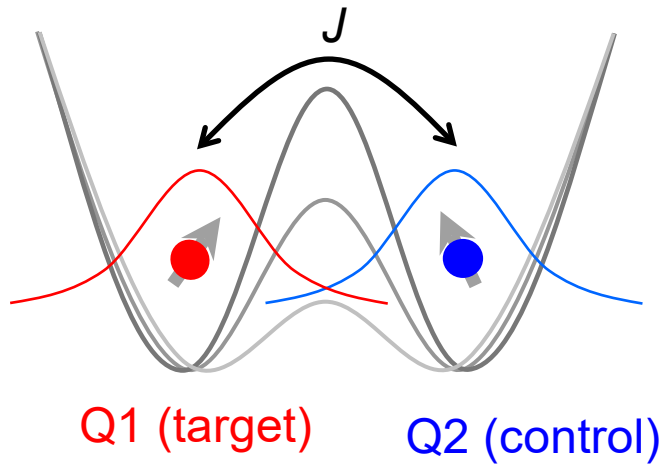
Single-qubit gate fidelity characterized by randomized benchmarking

|         | Q1      | Q2      | Q3      |
|---------|---------|---------|---------|
| nat. Si | 99.43 % | 99.57 % | 99.91 % |



# Two-Qubit Experiments using Two-spin States

Exchange coupling controlled by tunnel coupling

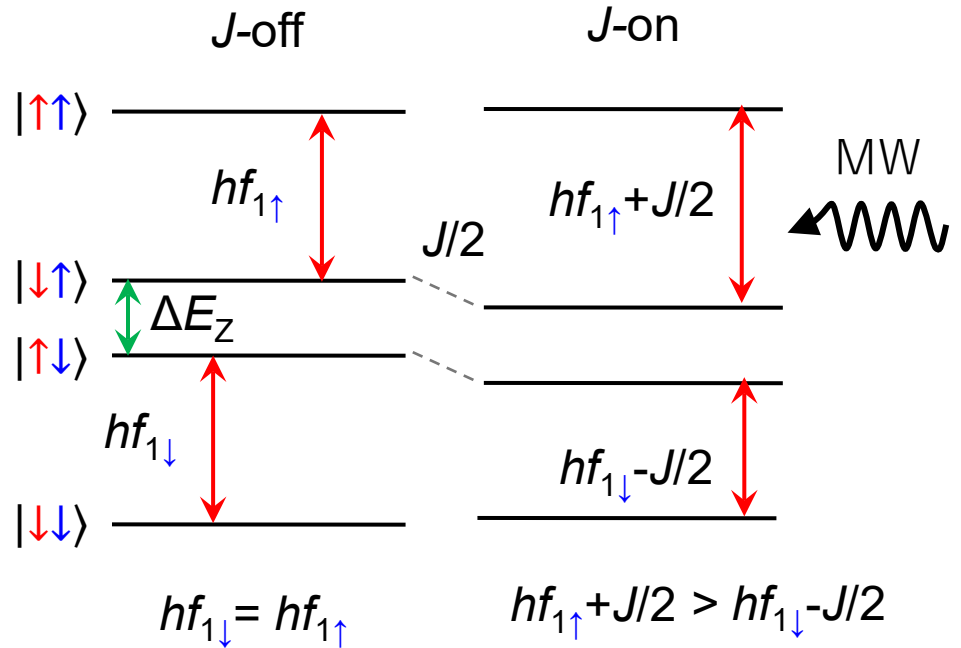


Magnetic field gradient ( $\Delta E_z$ ) induced by MM

$\Delta E_z \sim$  a few 100MHz  $\gg$   $J \sim$  10 MHz

“Heisenberg”      “Ising”

$$H_{\text{int}} = \frac{J}{4} \boldsymbol{\sigma}_1 \cdot \boldsymbol{\sigma}_2 \approx \frac{J_{12}}{4} \sigma_{z1} \sigma_{z2}$$

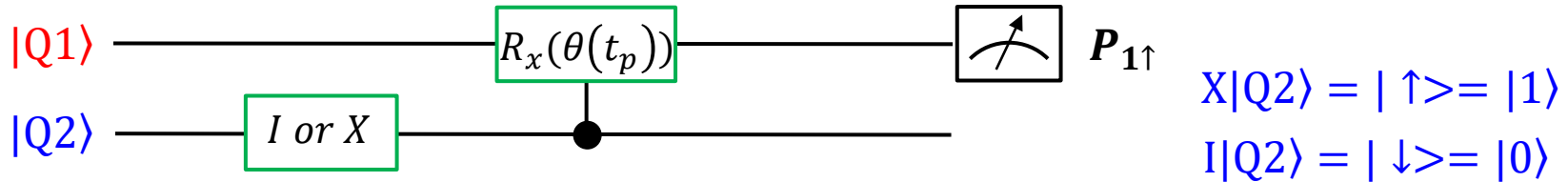


Useful for making  $\sqrt{SWAP}$ , CPHASE (CZ), and CROT (CNOT)

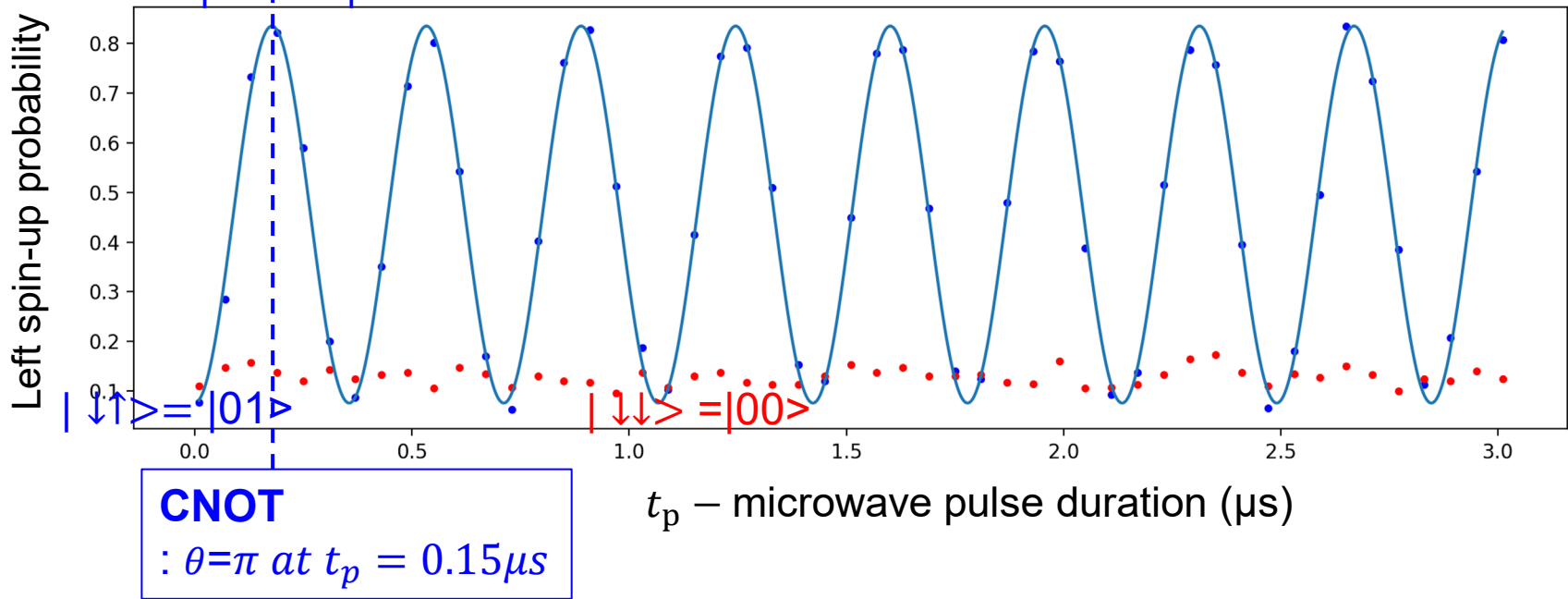
CROT:

When the upper transition is resonantly excited by MW, the left spin flips with the right spin up but not with the right spin down.

# Resonant-CROT

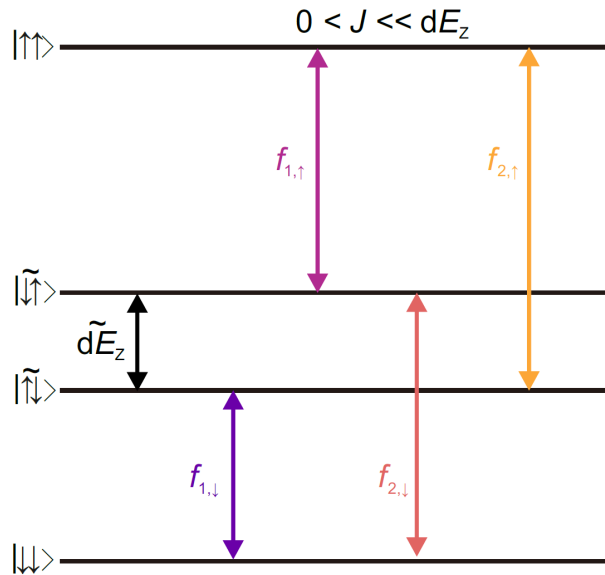


$|\uparrow\uparrow\rangle = |11\rangle$  Left spin rotation driven by MW



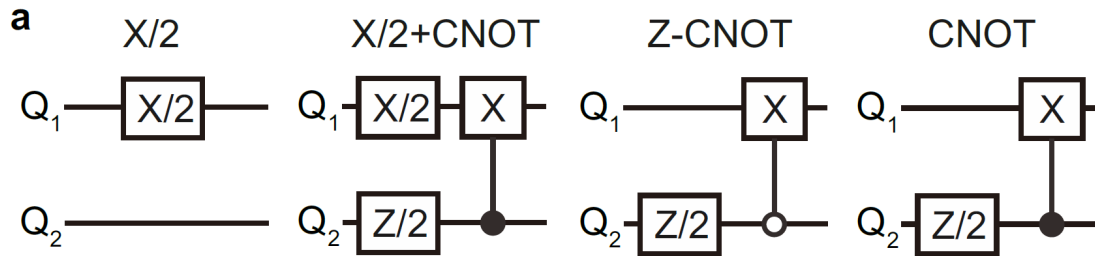
- Repeated flips of the left spin when the right spin up, while no flips when the right spin down.

# Two-qubit Gate Fidelity Assessed by Clifford-based Randomized Benchmarking



EDSR:  
Controlled-rotation  
(Rabi frequency  $< J$ )

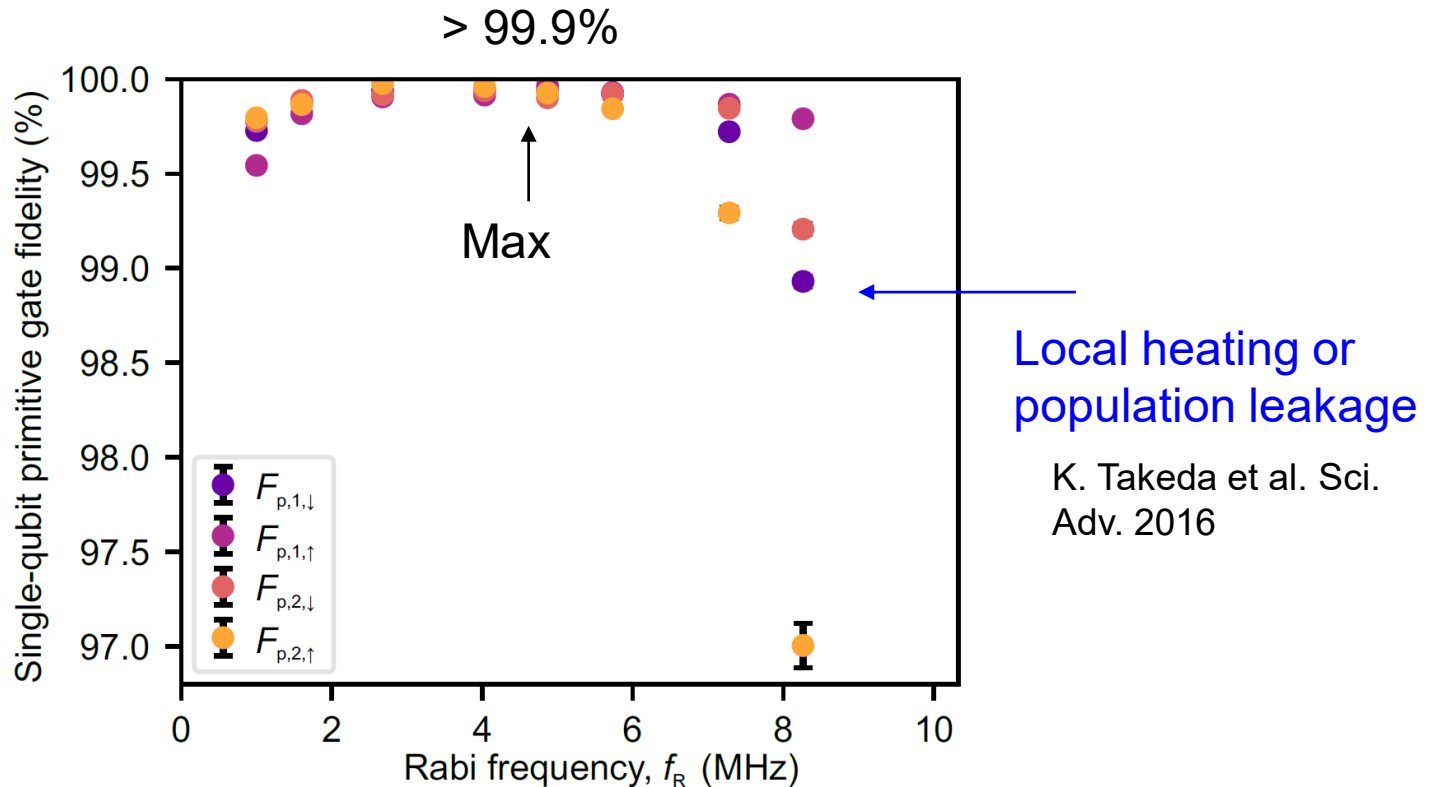
- All of the Clifford gates constructed from 8 primitive gates (controlled-rotation) and single-qubit phase gates under an exchange interaction.



All operated by single spin rotations

# Single-qubit Gate Fidelity for Two Qubits

A. Noiri et al. arXiv: 2108.02626 (2021)



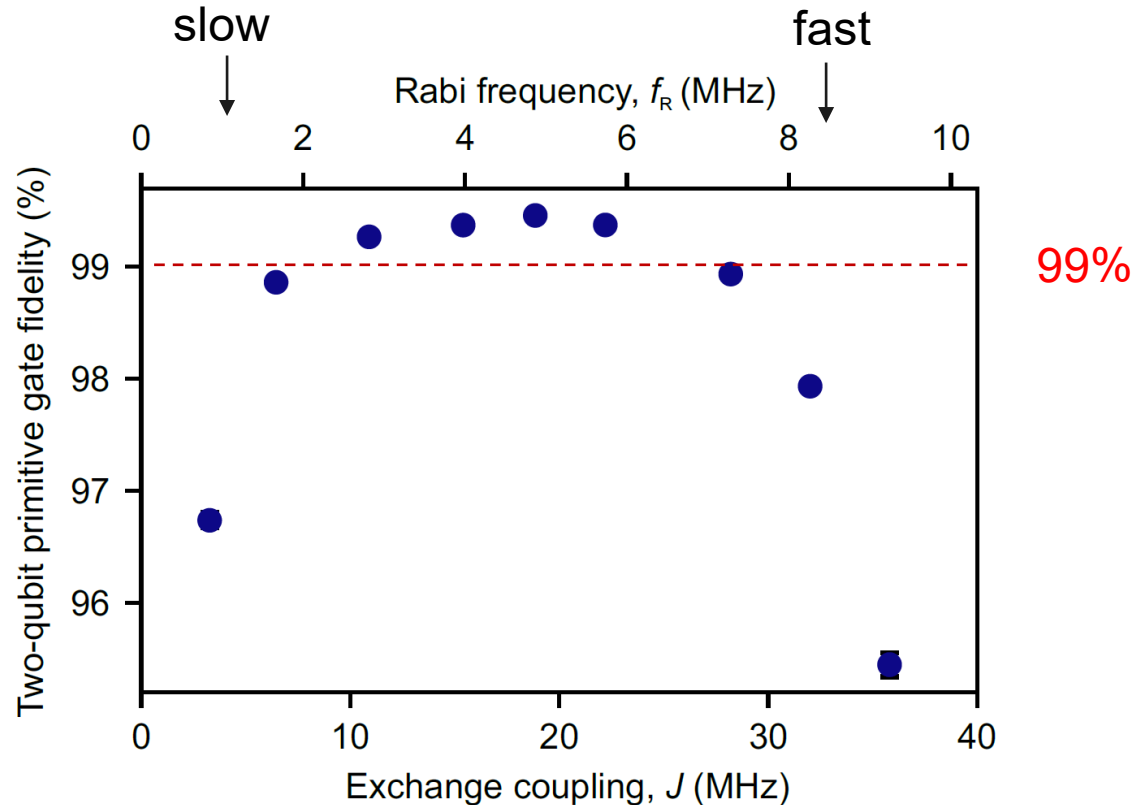
- Single qubit gate fidelity: increases as  $f_R$  increases because of the fast gating, but decreases for  $f_R > 5$  MHz because of the heating.  
➡ The maximum fidelity > 99.9% at  $f_R \sim 5$  MHz.

# Optimization of Two-qubit Gate Performance

A. Noiri et al. arXiv: 2108.02626 (2021)

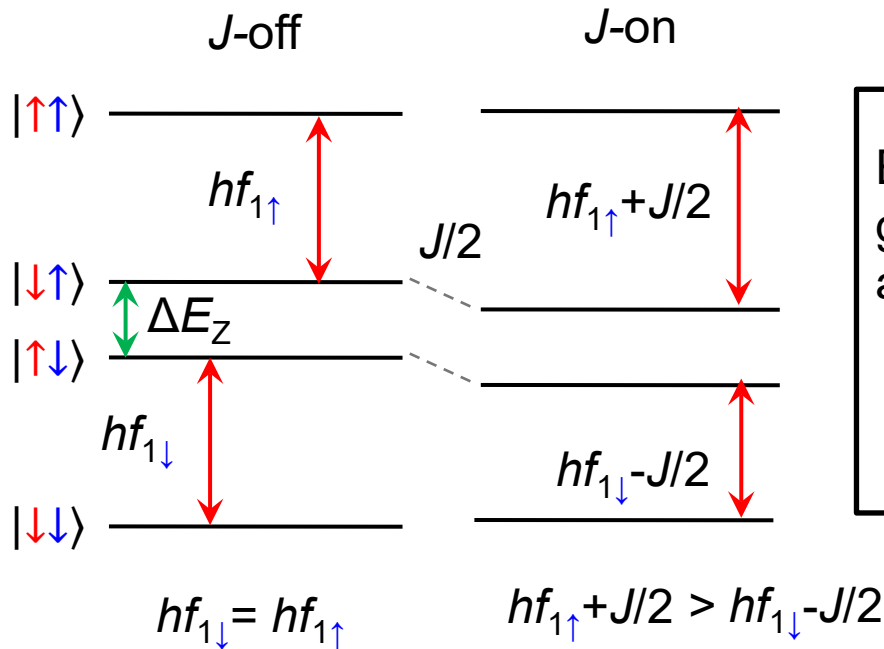
$$f_R = J/\sqrt{15}$$

Russ et al. PRB  
97. 085421 (2018)



- Dependence of the two-qubit gate fidelity is similar to that of the single qubit gate.
- The dephasing time only weakly depends on the exchange coupling.

# CPHSE (CZ) with Two Qubits



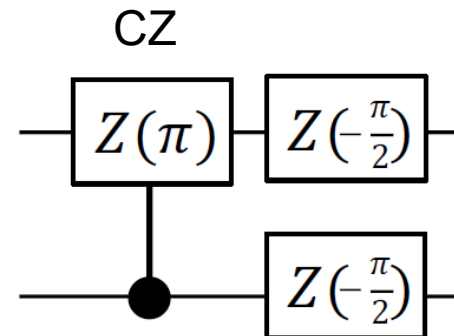
Energy shift  $\Delta E = J/2$  for time  $t$  generates a phase accumulation:

$$|\uparrow\downarrow\rangle \rightarrow e^{\frac{ijt}{2\hbar}} |\uparrow\downarrow\rangle = i |\uparrow\downarrow\rangle \quad \text{for } Jt = \frac{\pi}{\hbar}$$

| In                             | Out                             |
|--------------------------------|---------------------------------|
| $ \uparrow\uparrow\rangle$     | $+ \uparrow\uparrow\rangle$     |
| $ \uparrow\downarrow\rangle$   | $i \uparrow\downarrow\rangle$   |
| $ \downarrow\uparrow\rangle$   | $i \downarrow\uparrow\rangle$   |
| $ \downarrow\downarrow\rangle$ | $+ \downarrow\downarrow\rangle$ |

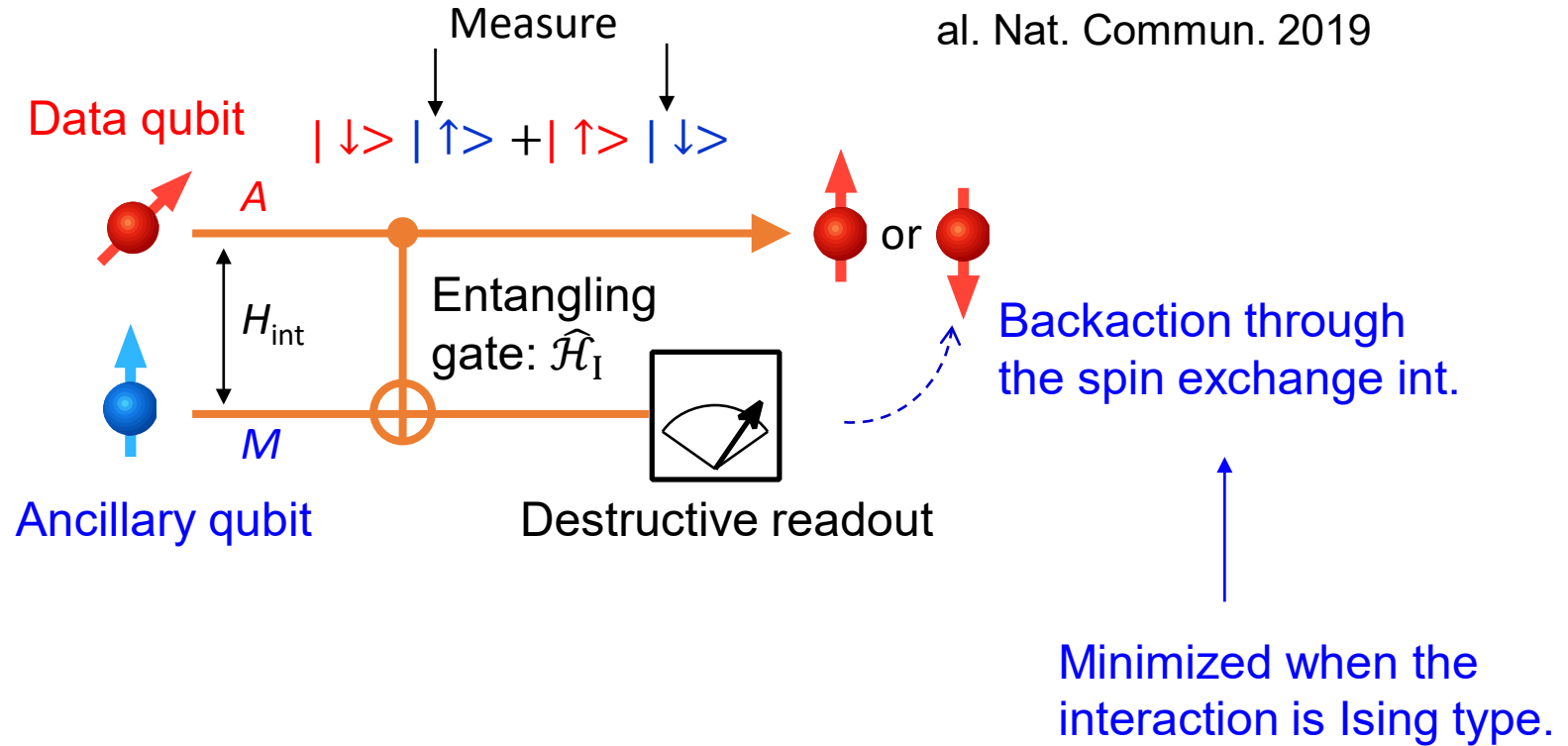
$$\begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & i & 0 & 0 \\ 0 & 0 & i & 0 \\ 0 & 0 & 0 & 1 \end{pmatrix}$$

**def**



# Quantum Non-demolition Measurement Scheme

T. Nakajima et al. Nat. Nanotechnol. 2018; J. Yoneda et al. Nat. Commun. 2019



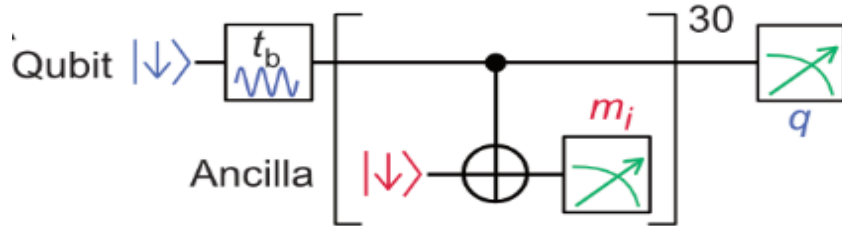
$$H_{\text{int}} = \frac{J}{4} \boldsymbol{\sigma}_1 \cdot \boldsymbol{\sigma}_2 \approx \frac{J_{12}}{4} \sigma_{z1} \sigma_{z2}$$



# Cumulative QND Readout of a Data Qubit

J. Yoneda et al. Nat. Commun. 2019

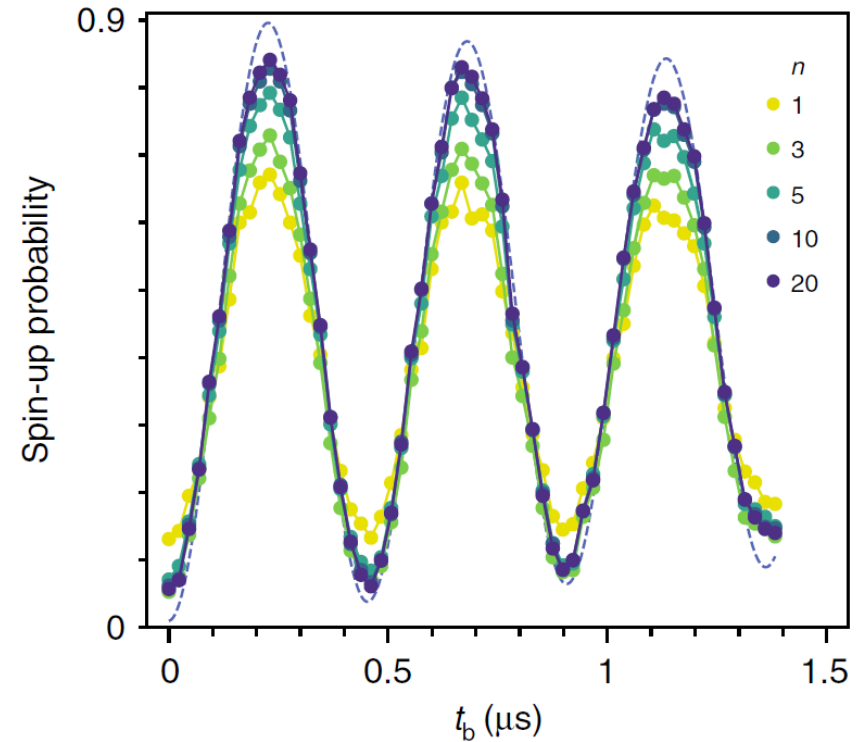
Repeatedly measure the ancilla to non-demolitionally read out the data bit Rabi



n=1 : F = 88% for  $|\downarrow\rangle$  and 73% for  $|\uparrow\rangle$   
 n=20: F = 96% for  $|\downarrow\rangle$  and 95% for  $|\uparrow\rangle$

➔ QND readout fidelity: 99.9% for  $|\downarrow\rangle$  and 97.7% for  $|\uparrow\rangle$  in the limit.

Data qubit Rabi



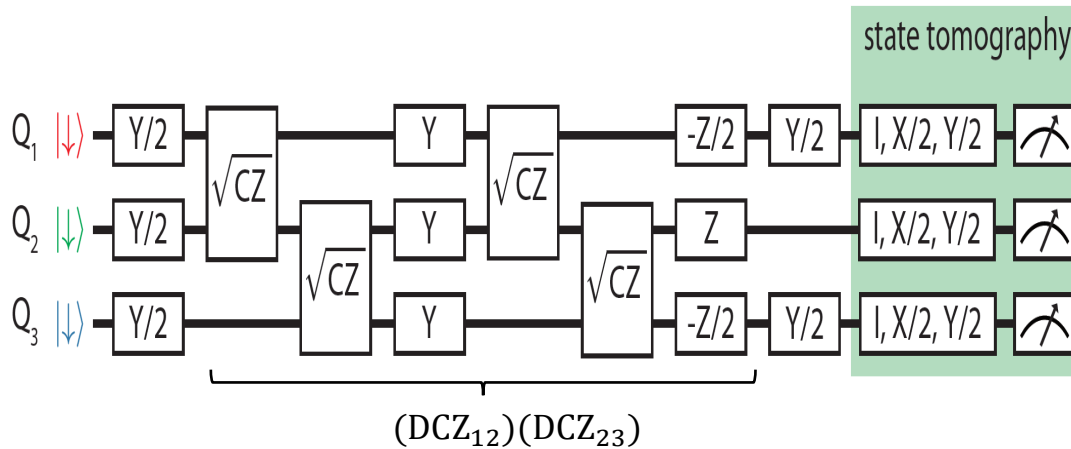
Measurement cycle = 60  $\mu$ sec

Note: data qubit T1 = 78 ms and 2.5 ms for down-spin and up-spin, respectively.

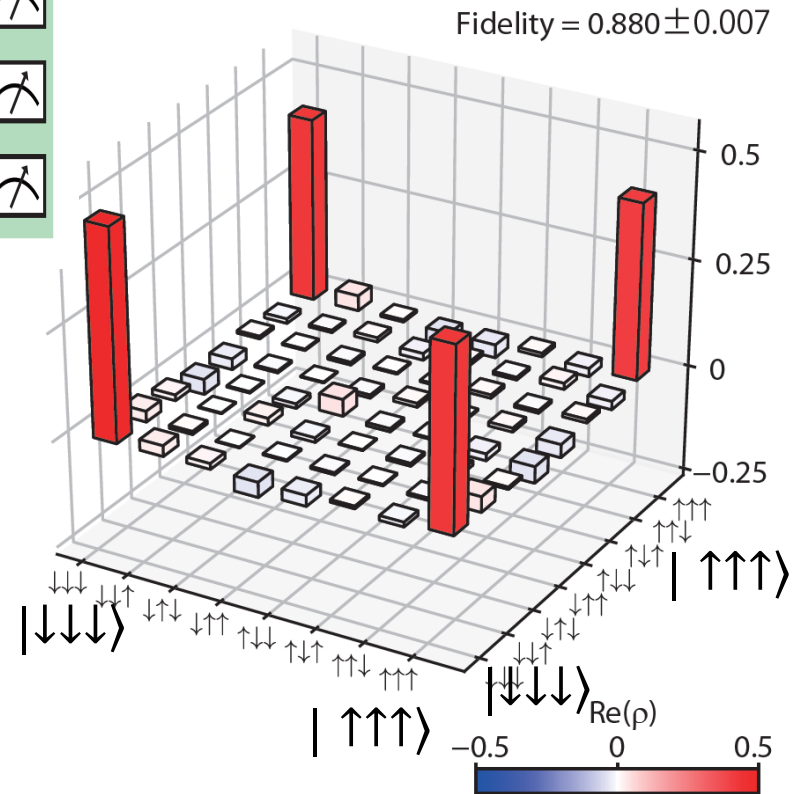
# Three-qubit Entanglement Generation

K. Takeda et al. Nat. Nanotechnol. 2021

$$|\text{GHZ}\rangle = (|\uparrow\uparrow\uparrow\rangle + |\downarrow\downarrow\downarrow\rangle)/\sqrt{2}$$



- $F = 0.88$  derived from quantum state tomography > (biseparable limit = 0.5 and W-state limit = 0.75)
- Violation of 3-qubit Bell's inequality:  
 $|\langle XXX \rangle - \langle YYX \rangle - \langle YXY \rangle - \langle XYY \rangle| > 2$



# Summary

## Single qubit gate

- Fidelity > 99.9% in  $^{28}\text{Si}/\text{SiGe}$  using a MM tech. for speeding up Rabi

## Two qubit gates

- Fidelity > 99% in  $^{28}\text{Si}/\text{SiGe}$  by optimizing Rabi speed and using a long dephasing time

## Readout and initialization

- Fidelity > 99% possible using QND measurement

## Three qubit device

- Three qubits with fidelity > 99.9 % in  $^{28}\text{Si}/\text{SiGe}$
- Three qubit entanglement, GHZ state with 88% fidelity

# Collaboration

Riken RQC, CEMS

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